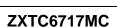




A Product Line of Diodes Incorporated



COMPLEMENTARY 15V NPN & 12V PNP LOW SATURATION TRANSISTOR

Features

NPN Transistor

- BV_{CEO} > 15V
 - I_C = 4.5A Continuous Collector Current
 - Low Saturation Voltage (100mV max @ 1A)
 - $R_{SAT} = 45m\Omega$ for a low equivalent On-Resistance

PNP Transistor

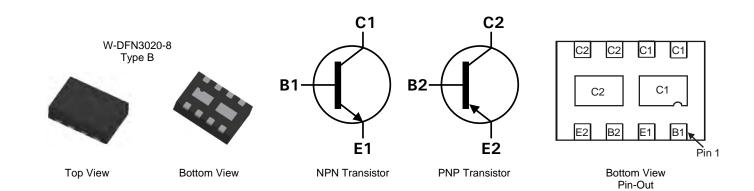
- BV_{CEO} > -12V
- I_C = -4A Continuous Collector Current
- Low Saturation Voltage (-140mV max @ -1A)
- $R_{SAT} = 60m\Omega$ for a low equivalent On-Resistance
- hFE characterized up to 12A for high current gain hold up
- Low profile 0.8mm high package for thin applications
- R_{0JA} efficient, 40% lower than SOT26
- 6mm² footprint, 50% smaller than TSOP6 and SOT26
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP capable (Note 4)

Mechanical Data

- Case: W-DFN3020-8 Type B
- Nominal package height: 0.8mm
- Case material: molded plastic. "Green" molding compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @
- Weight: 0.013 grams (approximate)

Applications

- DC DC Converters
- Charging circuits
- Power switches
- Motor control
- LED Backlighting circuits
- Portable applications



Ordering Information (Note 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTC6717MCTA	AEC-Q101	DA1	7	8	3,000
ZXTC6717MCQTA	Automotive	DA1	7	8	3,000

Notes:

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.

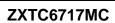
5. For packaging details, go to our website at http://www.diodes.com

Marking Information



DA1 = Product type Marking Code Dot denotes Pin 1





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	NPN	PNP	Unit
Collector-Base Voltage		V _{CBO}	40	-20	V
Collector-Emitter Voltage		V _{CEO}	15	-12	V
Emitter-Base Voltage		V _{EBO}	7	-7	V
Peak Pulse Current		I _{CM}	15	-12	А
Continuous Collector Current	(Notes 6 & 9)	- I _C	4.5	-4	^
Continuous Collector Current	(Notes 7 & 9)		5	-4.45	A
Base Current		Ι _Β	1		A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	NPN	PNP	Unit	
	(Notes 6 & 9)		1.5 12 2.45 19.6		w
Power Dissipation	(Notes 7 & 9)				
Linear Derating Factor	P _D 1.1 (Notes 8 & 9) 8		_	mW/°C	
	(Notes 8 & 10)	1	1.7 13.6		
	(Notes 6 & 9) (Notes 7 & 9)	-	83.3 51.0		-
Thermal Resistance, Junction to Ambient	(Notes 8 & 9) (Notes 8 & 10)	R _θ ja		111 °	
Thermal Resistance, Junction to Lead (Notes 9 & 11)		R _{θJL}	17.1		_
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to	+150	°C	

6. For a dual device surface mounted on 28mm x 28mm (8cm²) FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions; the device is Notes: measured when operating in a steady-state condition. The heatsink is split in half with the exposed collector pads connected to each half.

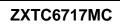
7. Same as note (6), except the device is measured at t <5 sec.
8. Same as note (6), except the device is surface mounted on 31mm x 31mm (10cm²) FR4 PCB with high coverage of single sided 1oz copper.

9. For a dual device with one active die.

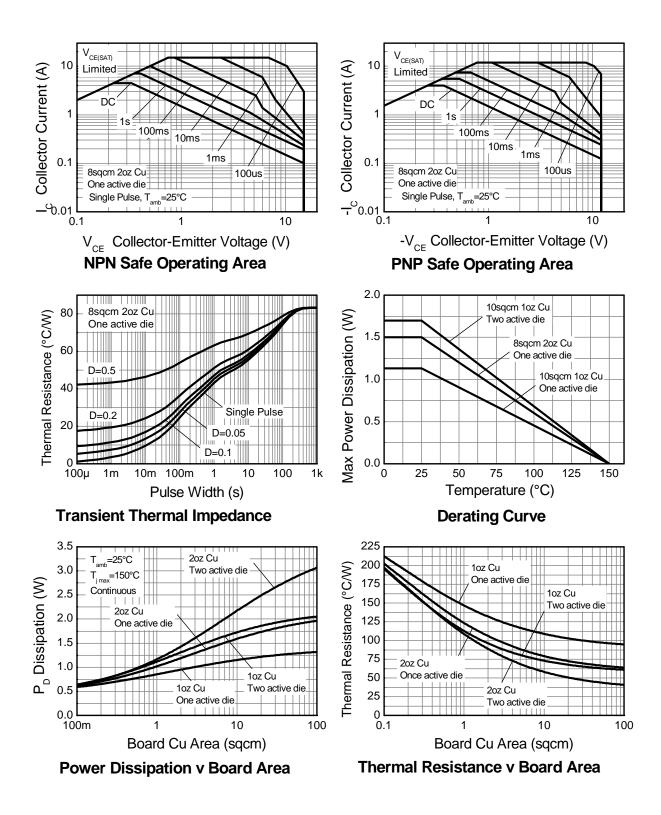
10. For dual device with 2 active die running at equal power.

11. Thermal resistance from junction to solder-point (on the exposed collector pads).

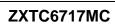




Thermal Characteristics and Derating Information







NPN - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

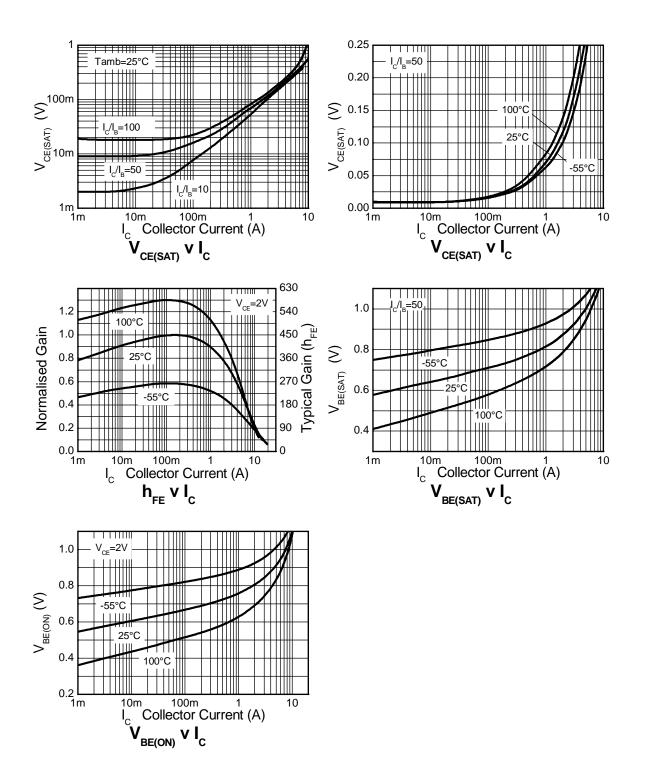
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	40	70	-	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 12)	BV _{CEO}	15	18	-	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.2	-	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	-	-	100	nA	$V_{CB} = 30V$
Emitter Cutoff Current	I _{EBO}	-	-	100	. nA	$V_{EB} = 6V$
Collector Emitter Cutoff Current	I _{CES}	-	-	100	nA	$V_{CE} = 12V$
Static Forward Current Transfer Ratio (Note 12)	hfe	200 300 200 150 -	415 450 320 240 80		-	$\begin{split} I_{C} &= 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 200 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 3 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 5 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 12 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 12)	V _{CE(sat)}	-	8 70 165 240 200	14 100 200 310 -	mV	$\begin{split} & I_{C} = 0.1A, \ I_{B} = 10mA \\ & I_{C} = 1A, \ I_{B} = 10mA \\ & I_{C} = 3A, \ I_{B} = 50mA \\ & I_{C} = 4.5A, \ I_{B} = 50mA \\ & I_{C} = 4.5A, \ I_{B} = 100mA \end{split}$
Base-Emitter Turn-On Voltage (Note 12)	V _{BE(on)}	-	0.88	0.96	V	$I_{C} = 4.5A, V_{CE} = 2V$
Base-Emitter Saturation Voltage (Note 12)	V _{BE(sat)}	-	0.94	1.05	V	$I_{C} = 4.5A, I_{B} = 50mA$
Output Capacitance	Cobo	-	30	40	pF	V _{CB} = 10V. f = 1MHz
Transition Frequency	f _T	80	120	-	MHz	$V_{CE} = 10V, I_C = 50mA,$ f = 100MHz
Turn-on Time	t _{on}	-	120	-	ns	$V_{CC} = 10V, I_{C} = 1A$
Turn-off Time	t _{off}	-	160	-	ns	$I_{B1} = I_{B2} = 10 \text{mA}$

Notes: 12. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

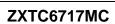


ZXTC6717MC

NPN – Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







Characteristic Symbol Min Max Unit **Test Condition** Тур $I_{\rm C} = -100 \mu A$ Collector-Base Breakdown Voltage -20 -35 **BV**CBO ٧ Collector-Emitter Breakdown Voltage (Note 12) -12 -25 V $I_{C} = -10 mA$ $\mathsf{BV}_{\mathsf{CEO}}$ _ Emitter-Base Breakdown Voltage -7 -8.5 V $I_{E} = -100 \mu A$ **BV**_{EBO} _ Collector Cutoff Current -100 - $V_{CB} = -16V$ Ісво nA Emitter Cutoff Current _ -100 nA $V_{EB} = -6V$ I_{EBO} $V_{CES} = -10V$ Collector Emitter Cutoff Current -100 nA -ICES $I_{C} = -10mA, V_{CE} = -2V$ 300 475 - $I_{C} = -100 \text{mA}, V_{CE} = -2 \text{V}$ 300 450 -Static Forward Current Transfer Ratio (Note 12) $I_C = -2.5A, V_{CE} = -2V$ h_{FE} 180 275 -60 100 - $I_{C} = -8A, V_{CE} = -2V$ 70 45 $I_{C} = -10A, V_{CE} = -2V$ $I_{C} = -0.1A, I_{B} = -10mA$ -10 -17 - $I_{C} = -1A, I_{B} = -10mA$ -140 -100 Collector-Emitter Saturation Voltage (Note 12) V_{CE(sat)} --100 -150 m٧ $I_{C} = -1.5A, I_{B} = -50mA$ -300 --195 $I_{\rm C} = -3A, I_{\rm B} = -50mA$ -240 -310 $I_{C} = -4A, I_{B} = -150mA$ Base-Emitter Turn-On Voltage (Note 12) --0.87 -0.96 V $I_{C} = -4A, V_{CE} = -2V$ V_{BE(on)} Base-Emitter Saturation Voltage (Note 12) -0.97 -1.07 $I_{C} = -4A, I_{B} = -150mA$ V V_{BE(sat)} -Output Capacitance 21 30 pF V_{CB} = -10V. f = 1MHz C_{obo} - $V_{CE} = -10V, I_C = -50mA,$ Transition Frequency 100 110 -MHz f_T f = 100MHz70 Turn-on Time $V_{CC} = -6V, I_C = -2A$ ns ton -130 Turn-off Time $I_{B1} = I_{B2} = -50 \text{mA}$ toff -ns

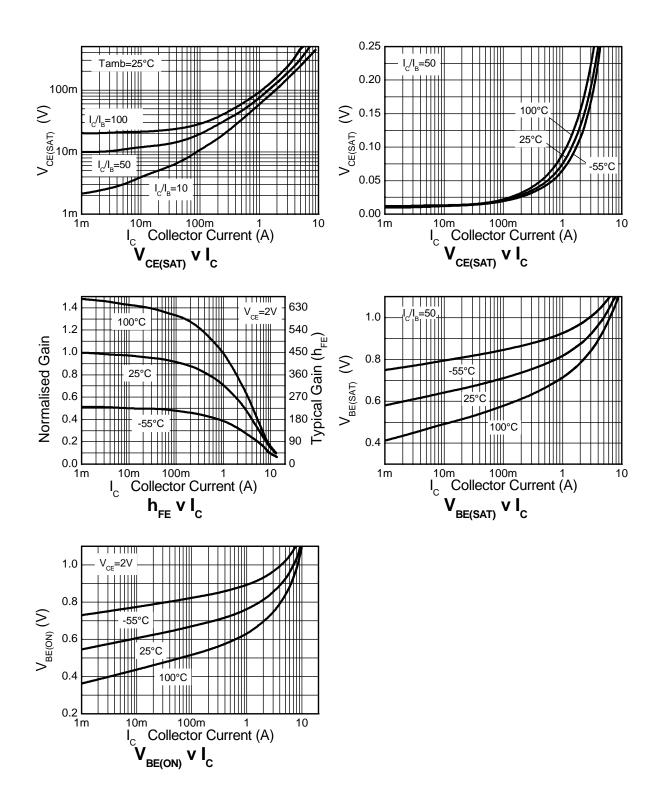
PNP - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Notes: 12. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



ZXTC6717MC

PNP – Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



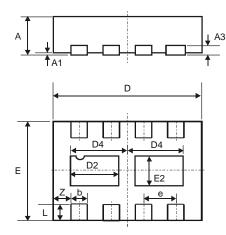




FX

Package Outline Dimensions

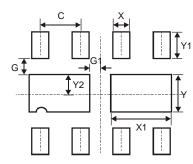
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



W-DFN3020-8 Type B				
Dim	Min	рев Мах	Тур	
Α	0.77	0.83	0.80	
A1	0	0.05	0.02	
A3	-	-	0.15	
b	0.25	0.35	0.30	
D	2.95	3.075	3.00	
D2	0.82	1.02	0.92	
D4	1.01	1.21	1.11	
е	-	-	0.65	
Е	1.95	2.075	2.00	
E2	0.43	0.63	0.53	
L	0.25	0.35	0.30	
Ζ	-	-	0.375	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
С	0.650			
G	0.285			
G1	0.090			
Х	0.400			
X1	1.120			
Y	0.730			
Y1	0.500			
Y2	0.365			



ZXTC6717MC

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